

# SILICON TRANSISTORS 2SC2958, 2959

# NPN SILICON EPITAXIAL TRANSISTOR FOR LOW-FREQUENCY POWER AMPLIFIERS

#### **FEATURES**

- Ideal for use of high voltage current such as TV vertical deflection (drive and output), audio output, pin cushion correction
- · Complementary transistor with 2SA1221 and 2SA1222

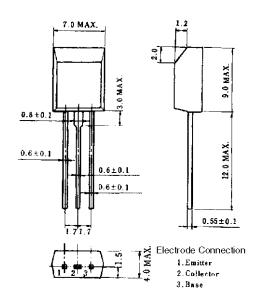
VCEO = 140 V: 2SA1221/2SC2958 VCEO = 160 V: 2SA1222/2SC2959

## ABSOLUTE MAXIMUM RATINGS (Ta = 25°C)

Parameter	Symbol	Ratings	Unit	
Collector to base voltage	Vсво	160	V	
Collector to emitter voltage	VCEO	140/160	V	
Emitter to base voltage	VEBO	5.0	V	
Collector current (DC)	Ic(DC)	500	mA	
Collector current (pulse)	IC(pulse)*	1.0	Α	
Total power dissipation	Рт	1.0	W	
Junction temperature	Tj	150	°C	
Storage temperature	T <sub>stg</sub>	−55 to +150 °C		

<sup>\*</sup> PW  $\leq$  10 ms, duty cycle  $\leq$  50%

# PACKAGE DRAWING (UNIT: mm)



# **ELECTRICAL CHARACTERISTICS (Ta = 25°C)**

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Collector cutoff current	Ісво	V <sub>CB</sub> = 100 V, I <sub>E</sub> = 0			200	nA
Emitter cutoff current	ІЕВО	V <sub>EB</sub> = 5.0 V, I <sub>C</sub> = 0			200	nA
DC current gain	hfe **	Vce = 2.0 V, Ic = 100 mA	100	150	400	
DC base voltage	V <sub>BE</sub> **	VcE = 5.0 V, Ic = 20 mA	0.6	0.64	0.7	V
Collector saturation voltage	V <sub>CE(sat)</sub> **	Ic = 1.0 A, I <sub>B</sub> = 0.2 A		0.32	0.7	V
Base saturation voltage	V <sub>BE(sat)</sub> **	Ic = 1.0 A, I <sub>B</sub> = 0.2 A		1.1	1.3	V
Output capacitance	Cob	V <sub>CB</sub> = 10 V, I <sub>E</sub> = 0, f = 1.0 MHz		13	30	pF
Gain bandwidth product	f⊤	$V_{CE} = 10 \text{ V}, \text{ I}_{E} = -20 \text{ mA}$	30	60		MHz

<sup>\*\*</sup> Pulse test PW  $\leq$  350  $\mu$ s, duty cycle  $\leq$  2% per pulsed

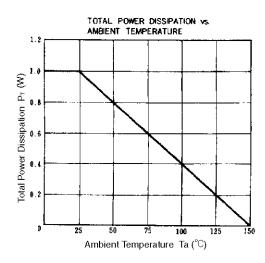
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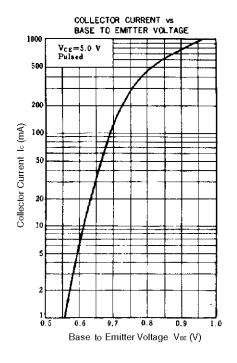


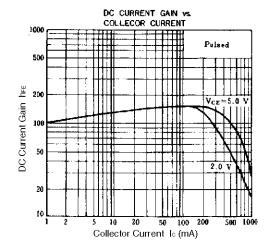
### **hfe CLASSIFICATION**

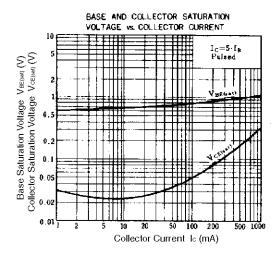
Marking	М	L	К
hfE	100 to 200	160 to 320	200 to 400

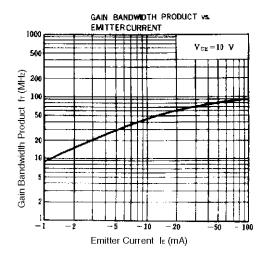
# TYPICAL CHARACTERISTICS (Ta = 25°C)

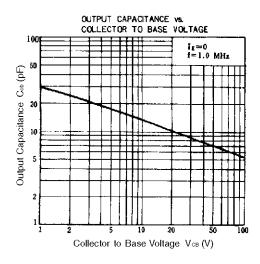












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